

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 10-163530

(43)Date of publication of application : 19.06.1998

(51)Int. CI.

H01L 33/00

H01L 31/10

H01S 3/18

(21)Application number : 08-315816

(71)Applicant : NICHIA CHEM IND LTD

(22)Date of filing : 27.11.1996

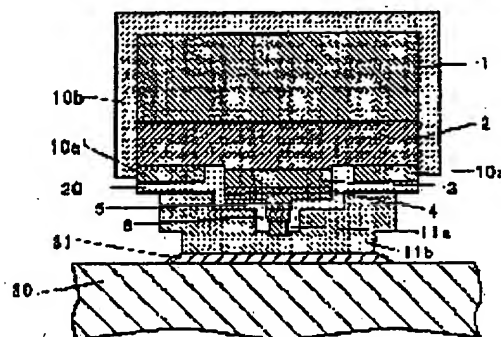
(72)Inventor : SENOO MASAYUKI
NAKAMURA SHUJI

(54) NITRIDE SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To reduce the contact resistance between a substrate and either an n-electrode or p-electrode by providing a semiconductor layer and the n- and p-electrodes on the first main surface side of the substrate and a first electrode, continuously from the second major surface and side face of the substrate and connecting the first electrode to either one of the n- and p-electrodes and insulating the electrode from the other electrode by forming an insulating film on the first major surface side.

SOLUTION: On the first major surface side of a substrate 1, an n-type contact layer 2, an n-type clad layer 3, an active layer 4, a p-type clad layer 5, and a contact layer 6 are formed. Over nearly the entire surface of the contact layer 6, a p-type electrode 11a for ohmic contact, and a second electrode 11b which is connected to the electrode 11a are formed and stuck to a supporting body 30 with a conductive adhesive 31. On the second major surface side of the substrate 1, n-electrodes 10a and 10a' are formed, and a first electrode 10b which is connected to the electrodes 10a and 10a' is formed continuously from the second major surface and the side face of the substrate 1. The electrode 10b is insulated from the p-electrode 11a and second electrode 11b by an insulating film 20, formed on the first major surface of the substrate 1.



LEGAL STATUS

[Date of request for examination] 12.02.1999

[Date of sending the examiner's decision
of rejection]

Searching PAJ

[Kind of final disposal of application
other than the examiner's decision of
rejection or application converted
registration]

[Date of final disposal for application]

[Patent number]

3087831

[Date of registration]

14.07.2000

[Number of appeal against examiner's
decision of rejection]

[Date of requesting appeal against
examiner's decision of rejection]

[Date of extinction of right]

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